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Product Change Notification

Product Group: SIL/Thursday August 6, 2026/PCN-SIL-000505-2026-REV-0



Additional Wafer Fabrication Capacity for Vishay Siliconix ICs for SIC645xx

For further information, please contact your regional Vishay office.

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Description of Change: Vishay Siliconix has expanded MOSFET production capacity by qualifying Vanguard International Semiconductor, Fab 3 in Taiwan as an additional foundry supplier.

Reason for Change: The additional MOSFET fabrication location has been qualified to increase manufacturing capacity and to provide an alternate geographic location for production.

Expected Influence on Quality/Reliability/Performance: There will be no negative effect on performance, quality or reliability.

Part Numbers/Series/Families Affected: SIC645ADR-T1-GE3, SIC645AER-T1-GE3, SIC645ALR-T1-GE3, SIC645ER-T1-GE3,

Vishay Brand(S): Vishay Siliconix

Time Schedule:

Start Shipment Date: Thursday October 15, 2026

Sample Availability: Samples will be available starting September 1, 2026

Product Identification: Lot number

Qualification Data: Please see attached.

This PCN is considered approved, without further notification, unless we receive specific customer concerns before Thursday October 1, 2026 or as specified by contract.

Issued By: Lisette Saba, malinalisette.saba@vishay.com



Qualification Data

July 2026



Reliability Test Result

EVAL	STRESS	STEP	TEST	CONDITION	HR-CYC	S	S	FAIL	DONE	TEST	FAIL
*****	*****	****	*****	*****	*****	****	****	****	****	TYPE	CODE
2660062	DYN OP LIF	0	DYN OP	LF (12	0	82		0	X	ET	
		1	DYN OP	LF (12	168	82		0	X	ET	
	ESD - C D	0	ESD'	- C D MO	0	28		0	X	ET	
		1	ESD'	- C D MO	125	3		0	X	ET	
		2	ESD'	- C D MO	250	3		0	X	ET	
		3	ESD'	- C D MO	500	3		0	X	ET	
		4	ESD'	- C D MO	750	3		0	X	ET	
		5	ESD'	- C D MO	1000	3		0	X	ET	
		6	ESD'	- C D MO	1500	3		0	X	ET	
		7	ESD'	- C D MO	2000	10		0	X	ET	
	ESD - H B	0	ESD'	- H B MO	0	27		0	X	ET	
		1	ESD'	- H B MO	125	3		0	X	ET	
		2	ESD'	- H B MO	500	3		0	X	ET	
		3	ESD'	- H B MO	1000	3		0	X	ET	
		4	ESD'	- H B MO	1500	3		0	X	ET	
		5	ESD'	- H B MO	2000	3		0	X	ET	
		6	ESD'	- H B MO	2500	3		0	X	ET	
		7	ESD'	- H B MO	3000	3		0	X	ET	
		8	ESD'	- H B MO	3500	3		0	X	ET	
		9	ESD'	- H B MO	4000	3		0	X	ET	
	LATCH-UP	0	LATCH-UP		0	36		0	X	ET	
		1	LATCH-UP		100	6		0	X	ET	
		2	LATCH-UP		150	6		0	X	ET	
		3	LATCH-UP		200	6		0	X	ET	
		4	LATCH-UP		300	6		0	X	ET	
		5	LATCH-UP		400	6		0	X	ET	
		6	LATCH-UP		500	6		0	X	ET	

PART NUMBER: SIC645AER
 LOT ID: V26V028.58
 PURPOSE: QUALIFICATION



MOSFET Qualification Result

Part number/ Geometry	EBR#/LOT ID	RELIABILITY EVAL#	STRESS	Test Point	No. of Lots	No. Of Samples	Result
SIC645AER	V26V028.58	2660062	HTOL	168 Hrs	1	82	Passed
			ESD - CDM	2000 V	1	3	Passed
			ESD-HBM	4000 V	1	3	Passed
			Latch-Up	500mA @25C	1	6	Passed
				300mA at 125C	1	6	Passed
NEWG28EZPW8VS	EBR426	1966409	ESD - CDM	1000	1	10	Passed
			ESD - HBM	500 V	1	10	Passed
		1980593	RTRB	168 Hrs	1	82	Passed
			HTRB	500 Hrs	1	82	Passed
			HTGB	500 Hrs	1	82	Passed
NEWH28FZSG8VS		1966410	ESD - CDM	1000 V	1	10	Passed
			ESD - HBM	1850 V	1	10	Passed
		1980594	RTRB	168 Hrs	1	82	Passed
			HTRB	500 Hrs	1	82	Passed
			HTGB	500 Hrs	1	82	Passed

SIC645ADR-T1-GE3 SIC645AER-T1-GE3 SIC645ALR-T1-GE3 SIC645ER-T1-GE3